

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED




BAT54W-MS

Product specification

Features

- Low Forward Voltage Drop
- Fast Switching
- Small Surface Mount Package
- PN Junction Guard Ring for Transient and ESD Protection
- Available in Lead Free Version

Reference News

PACKAGE OUTLINE	PIN Configuration	MARKING
 SOD-123		

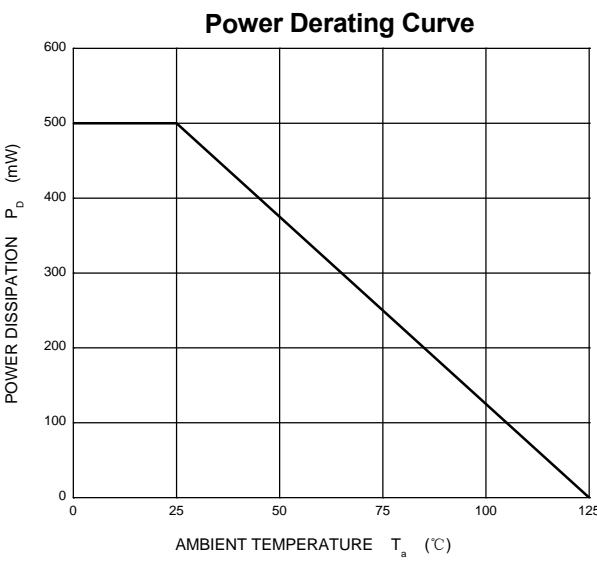
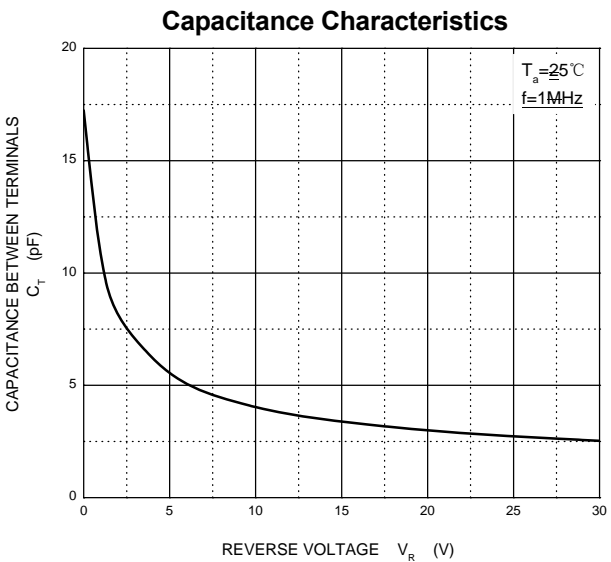
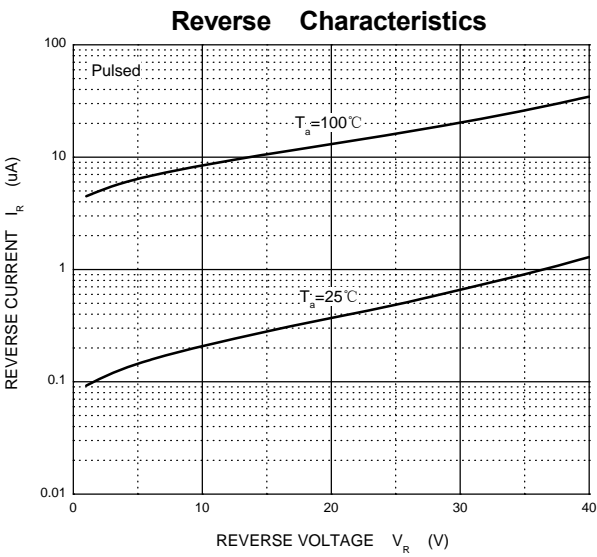
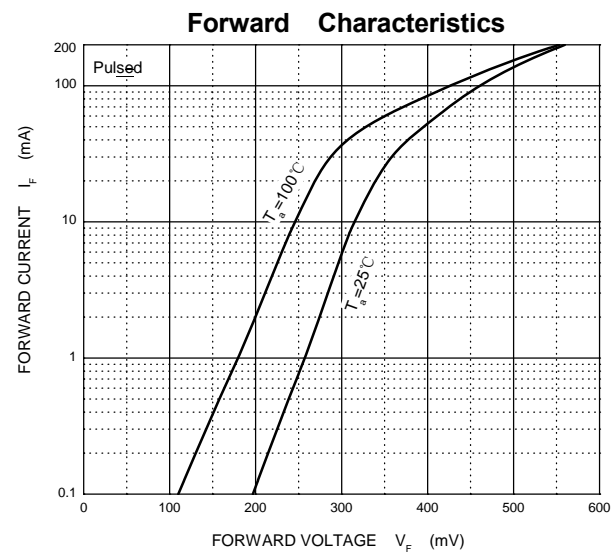
Maximum Ratings @Ta=25℃

Parameter	Symbol	Limit	Unit
DC blocking voltage	V_R	30	V
RMS reverse voltage	$V_{R(RMS)}$	21	
Average rectified output current	I_o	100	mA
Forward continuous current	I_F	200	mA
Repetitive peak forward current	I_{FRM}	300	mA
Non-repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	600	mA
Power dissipation	P_d	500	mW
Thermal resistance junction to ambient	$R_{\theta JA}$	200	℃/W
Junction temperature	T_J	125	℃
Storage temperature range	T_{STG}	-55~+150	℃

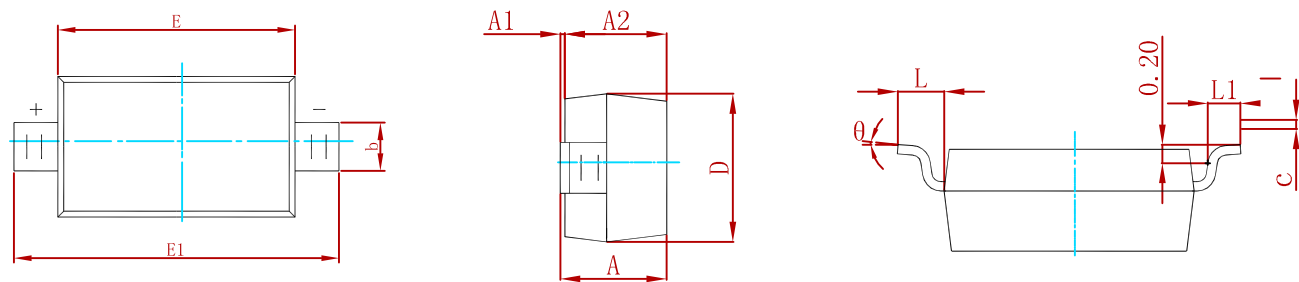
Electrical Characteristics @Ta=25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	30			V
Forward voltage	V_{F1}	$I_F=0.1mA$			240	mV
	V_{F2}	$I_F=1.0mA$			320	mV
	V_{F3}	$I_F=10mA$			400	mV
	V_{F4}	$I_F=30mA$			500	mV
	V_{F5}	$I_F=100mA$			1000	mV
Reverse current	I_R	$V_R=25V$			2.0	uA
Reverse recovery time	t_{rr}	$I_F=10mA, I_R=10mA$ to $1mA, R_L=100\Omega$			5.0	ns
Capacitance between terminals	C_T	$V_R=1V, f=1MHz$			10	pF

Typical Characteristics

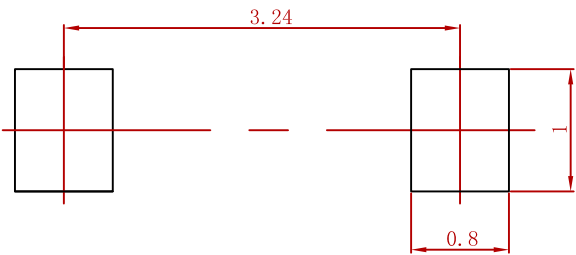


PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.450	0.650	0.018	0.026
c	0.080	0.150	0.003	0.006
D	1.500	1.700	0.059	0.067
E	2.600	2.800	0.102	0.110
E1	3.550	3.850	0.140	0.152
L	0.500 REF		0.020 REF	
L1	0.250	0.450	0.010	0.018
θ	0°	8°	0°	8°

Suggested Pad Layout



- Note:**
- 1.Controlling dimension:in millimeters.
 - 2.General tolerance:± 0.05mm.
 - 3.The pad layout is for reference purposes only.

REELSPECIFICATION

P/N	PKG	QTY
BAT54W-MS	SOD-123	3000

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